EXF



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Detail	s
	-

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	768
Total RAM Bits	-
Number of I/O	49
Number of Gates	30000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/agl030v2-qng68

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1 – IGLOO Device Family Overview

General Description

The IGLOO family of flash FPGAs, based on a 130-nm flash process, offers the lowest power FPGA, a single-chip solution, small footprint packages, reprogrammability, and an abundance of advanced features.

The Flash*Freeze technology used in IGLOO devices enables entering and exiting an ultra-low power mode that consumes as little as 5 μ W while retaining SRAM and register data. Flash*Freeze technology simplifies power management through I/O and clock management with rapid recovery to operation mode.

The Low Power Active capability (static idle) allows for ultra-low power consumption (from 12 μ W) while the IGLOO device is completely functional in the system. This allows the IGLOO device to control system power management based on external inputs (e.g., scanning for keyboard stimulus) while consuming minimal power.

Nonvolatile flash technology gives IGLOO devices the advantage of being a secure, low power, singlechip solution that is Instant On. IGLOO is reprogrammable and offers time-to-market benefits at an ASIClevel unit cost.

These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

IGLOO devices offer 1 kbit of on-chip, reprogrammable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on an integrated phase-locked loop (PLL). The AGL015 and AGL030 devices have no PLL or RAM support. IGLOO devices have up to 1 million system gates, supported with up to 144 kbits of true dual-port SRAM and up to 300 user I/Os.

M1 IGLOO devices support the high-performance, 32-bit Cortex-M1 processor developed by ARM for implementation in FPGAs. Cortex-M1 is a soft processor that is fully implemented in the FPGA fabric. It has a three-stage pipeline that offers a good balance between low power consumption and speed when implemented in an M1 IGLOO device. The processor runs the ARMv6-M instruction set, has a configurable nested interrupt controller, and can be implemented with or without the debug block. Cortex-M1 is available for free from Microsemi for use in M1 IGLOO FPGAs.

The ARM-enabled devices have ordering numbers that begin with M1AGL and do not support AES decryption.

Flash*Freeze Technology

The IGLOO device offers unique Flash*Freeze technology, allowing the device to enter and exit ultra-low power Flash*Freeze mode. IGLOO devices do not need additional components to turn off I/Os or clocks while retaining the design information, SRAM content, and registers. Flash*Freeze technology is combined with in-system programmability, which enables users to quickly and easily upgrade and update their designs in the final stages of manufacturing or in the field. The ability of IGLOO V2 devices to support a wide range of core voltage (1.2 V to 1.5 V) allows further reduction in power consumption, thus achieving the lowest total system power.

When the IGLOO device enters Flash*Freeze mode, the device automatically shuts off the clocks and inputs to the FPGA core; when the device exits Flash*Freeze mode, all activity resumes and data is retained.

The availability of low power modes, combined with reprogrammability, a single-chip and single-voltage solution, and availability of small-footprint, high pin-count packages, make IGLOO devices the best fit for portable electronics.

Table 2-21 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage

				Device	≩ Specific γ/₩/	Dynamic F VIHz)	'ower		
Parameter	Definition	AGL1000	AGL600	AGL400	AGL250	AGL125	AGL060	AGL030	AGL015
PAC1	Clock contribution of a Global Rib	4.978	3.982	3.892	2.854	2.845	1.751	0.000	0.000
PAC2	Clock contribution of a Global Spine	2.773	2.248	1.765	1.740	1.122	1.261	2.229	2.229
PAC3	Clock contribution of a VersaTile row	0.883	0.924	0.881	0.949	0.939	0.962	0.942	0.942
PAC4	Clock contribution of a VersaTile used as a sequential module	0.096	0.095	0.096	0.095	0.095	0.096	0.094	0.094
PAC5	First contribution of a VersaTile used as a sequential module				0.04	45			
PAC6	Second contribution of a VersaTile used as a sequential module				0.18	86			
PAC7	Contribution of a VersaTile used as a combinatorial module	0.158	0.149	0.158	0.157	0.160	0.170	0.160	0.155
PAC8	Average contribution of a routing net	0.756	0.729	0.753	0.817	0.678	0.692	0.738	0.721
PAC9	Contribution of an I/O input pin (standard-dependent)		See Table	2-13 on pa	ge 2-10 thr	rough Table	∋ 2-15 on p	age 2-11.	
PAC10	Contribution of an I/O output pin (standard-dependent)		See Table	2-16 on pa	ige 2-11 thr	rough Table	32-18 on p	age 2-12.	
PAC11	Average contribution of a RAM block during a read operation				25.0	00			
PAC12	Average contribution of a RAM block during a write operation				30.0	00			
PAC13	Dynamic PLL contribution				2.1	10			

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Microsemi Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-23 on page 2-19.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-24 on page 2-19.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-24 on page 2-19. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

 $P_{TOTAL} = P_{STAT} + P_{DYN}$

 $\mathsf{P}_{\mathsf{STAT}}$ is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—PSTAT

P_{STAT} = (P_{DC1} or P_{DC2} or P_{DC3}) + N_{BANKS} * P_{DC5} + N_{INPUTS} * P_{DC6} + N_{OUTPUTS} * P_{DC7}

N_{INPUTS} is the number of I/O input buffers used in the design.

N_{OUTPUTS} is the number of I/O output buffers used in the design.

N_{BANKS} is the number of I/O banks powered in the design.

Total Dynamic Power Consumption—PDYN

 $P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

 $P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * P_{AC3} + N_{S-CELL} * P_{AC4}) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the *IGLOO FPGA Fabric User Guide.*

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the *IGLOO FPGA Fabric User Guide*.

 $\mathsf{F}_{\mathsf{CLK}}$ is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

P_{AC1}, P_{AC2}, P_{AC3}, and P_{AC4} are device-dependent.

Sequential Cells Contribution—P_{S-CELL}

 $\mathsf{P}_{\text{S-CELL}} = \mathsf{N}_{\text{S-CELL}} * (\mathsf{P}_{\text{AC5}} + \alpha_1 / 2 * \mathsf{P}_{\text{AC6}}) * \mathsf{F}_{\text{CLK}}$

 N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

 α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

 F_{CLK} is the global clock signal frequency.

Table 2-60 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	2.89	0.26	0.97	1.10	2.93	2.38	2.53	2.96	8.72	8.17	ns
4 mA	Std.	1.55	2.89	0.26	0.97	1.10	2.93	2.38	2.53	2.96	8.72	8.17	ns
6 mA	Std.	1.55	2.50	0.26	0.97	1.10	2.54	2.04	2.77	3.37	8.33	7.82	ns
8 mA	Std.	1.55	2.50	0.26	0.97	1.10	2.54	2.04	2.77	3.37	8.33	7.82	ns
12 mA	Std.	1.55	2.31	0.26	0.97	1.10	2.34	1.86	2.93	3.64	8.12	7.65	ns
16 mA	Std.	1.55	2.31	0.26	0.97	1.10	2.34	1.86	2.93	3.64	8.12	7.65	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-61 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V Applicable to Standard Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
2 mA	Std.	1.55	4.39	0.26	0.94	1.10	4.46	3.91	2.17	2.44	ns
4 mA	Std.	1.55	4.39	0.26	0.94	1.10	4.46	3.91	2.17	2.44	ns
6 mA	Std.	1.55	3.72	0.26	0.94	1.10	3.78	3.43	2.40	2.85	ns
8 mA	Std.	1.55	3.72	0.26	0.94	1.10	3.78	3.43	2.40	2.85	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-62 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V Applicable to Standard Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
2 mA	Std.	1.55	2.74	0.26	0.94	1.10	2.78	2.26	2.17	2.55	ns
4 mA	Std.	1.55	2.74	0.26	0.94	1.10	2.78	2.26	2.17	2.55	ns
6 mA	Std.	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns
8 mA	Std.	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-69 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V
Applicable to Standard Plus Banks

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t _{dout}	t _{DP}	t _{DIN}	t _{PY}	t _{eout}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
100 µA	2 mA	Std.	0.97	5.84	0.18	1.20	0.66	5.86	5.04	2.74	2.71	9.46	8.64	ns
100 µA	4 mA	Std.	0.97	5.84	0.18	1.20	0.66	5.86	5.04	2.74	2.71	9.46	8.64	ns
100 µA	6 mA	Std.	0.97	4.76	0.18	1.20	0.66	4.78	4.33	3.09	3.33	8.37	7.93	ns
100 µA	8 mA	Std.	0.97	4.76	0.18	1.20	0.66	4.78	4.33	3.09	3.33	8.37	7.93	ns
100 µA	12 mA	Std.	0.97	4.02	0.18	1.20	0.66	4.04	3.78	3.33	3.73	7.64	7.37	ns
100 µA	16 mA	Std.	0.97	4.02	0.18	1.20	0.66	4.04	3.78	3.33	3.73	7.64	7.37	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 μA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-70 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V
Applicable to Standard Plus Banks

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t _{dout}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
100 µA	2 mA	Std.	0.97	3.33	0.18	1.20	0.66	3.35	2.68	2.73	2.88	6.94	6.27	ns
100 µA	4 mA	Std.	0.97	3.33	0.18	1.20	0.66	3.35	2.68	2.73	2.88	6.94	6.27	ns
100 µA	6 mA	Std.	0.97	2.75	0.18	1.20	0.66	2.77	2.17	3.08	3.50	6.36	5.77	ns
100 µA	8 mA	Std.	0.97	2.75	0.18	1.20	0.66	2.77	2.17	3.08	3.50	6.36	5.77	ns
100 µA	12 mA	Std.	0.97	2.45	0.18	1.20	0.66	2.47	1.92	3.33	3.90	6.06	5.51	ns
100 µA	16 mA	Std.	0.97	2.45	0.18	1.20	0.66	2.47	1.92	3.33	3.90	6.06	5.51	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 μA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

3. Software default selection highlighted in gray.

Table 2-100 • 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	0.97	3.25	0.18	1.01	0.66	3.21	3.25	2.33	1.61	6.80	6.85	ns
4 mA	Std.	0.97	2.62	0.18	1.01	0.66	2.68	2.51	2.66	2.46	6.27	6.11	ns
6 mA	Std.	0.97	2.31	0.18	1.01	0.66	2.36	2.15	2.90	2.87	5.95	5.75	ns
8 mA	Std.	0.97	2.25	0.18	1.01	0.66	2.30	2.08	2.95	2.98	5.89	5.68	ns
12 mA	Std.	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns
16 mA	Std.	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-101 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	0.97	5.78	0.18	1.01	0.66	5.90	5.32	1.95	1.47	9.49	8.91	ns
4 mA	Std.	0.97	4.75	0.18	1.01	0.66	4.85	4.54	2.25	2.21	8.44	8.13	ns
6 mA	Std.	0.97	4.07	0.18	1.01	0.66	4.15	3.98	2.46	2.58	7.75	7.57	ns
8 mA	Std.	0.97	4.07	0.18	1.01	0.66	4.15	3.98	2.46	2.58	7.75	7.57	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-102 • 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
2 mA	Std.	0.97	2.76	0.18	1.01	0.66	2.79	2.76	1.94	1.51	6.39	6.35	ns
4 mA	Std.	0.97	2.25	0.18	1.01	0.66	2.30	2.09	2.24	2.29	5.89	5.69	ns
6 mA	Std.	0.97	1.97	0.18	1.01	0.66	2.02	1.76	2.46	2.66	5.61	5.36	ns
8 mA	Std.	0.97	1.97	0.18	1.01	0.66	2.02	1.76	2.46	2.66	5.61	5.36	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-103 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V Applicable to Standard Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
2 mA	Std.	0.97	5.63	0.18	0.98	0.66	5.74	5.30	1.68	1.24	ns
4 mA	Std.	0.97	4.69	0.18	0.98	0.66	4.79	4.52	1.97	1.98	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-123 • 1.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core VoltageCommercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 VApplicable to Standard Plus Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	6.43	0.26	1.27	1.10	6.54	5.95	2.82	2.83	12.32	11.74	ns
4 mA	Std.	1.55	5.59	0.26	1.27	1.10	5.68	5.27	3.07	3.27	11.47	11.05	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-124 • 1.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
2 mA	Std.	1.55	3.02	0.26	1.27	1.10	3.07	2.81	2.82	2.92	8.85	8.59	ns
4 mA	Std.	1.55	2.68	0.26	1.27	1.10	2.72	2.39	3.07	3.37	8.50	8.18	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-125 • 1.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V Applicable to Standard Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
2 mA	Std.	1.55	6.35	0.26	1.22	1.10	6.46	5.93	2.40	2.46	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-126 • 1.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V Applicable to Standard Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
2 mA	Std.	1.55	2.92	0.26	1.22	1.10	2.96	2.60	2.40	2.56	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Test Point
Datapath
$$\downarrow$$
 5 pF
 $R = 1 k$
Enable Path \downarrow R to VCCI for $t_{LZ} / t_{ZL} / t_{ZLS}$
 R to GND for $t_{HZ} / t_{ZH} / t_{ZHS}$
 $5 pF for t_{ZH} / t_{ZHS} / t_{ZL} / t_{ZLS}$

Figure 2-11 • AC Loading

Table 2-130 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.2	0.6	5

Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.

Timing Characteristics

1.2 V DC Core Voltage

Table 2-131 • 1.2 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
2 mA	Std.	1.55	8.37	0.26	1.60	1.10	8.04	7.17	3.94	3.52	13.82	12.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-132 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
2 mA	Std.	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-133 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	7.59	0.26	1.59	1.10	7.29	6.54	3.30	3.35	13.08	12.33	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-134 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.59	1.10	3.11	2.78	3.29	3.48	8.90	8.57	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.





Timing Characteristics

1.5 V DC Core Voltage

Table 2-171 • Register Delays

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t _{CLKQ}	Clock-to-Q of the Core Register	0.89	ns
t _{SUD}	Data Setup Time for the Core Register	0.81	ns
t _{HD}	Data Hold Time for the Core Register	0.00	ns
t _{SUE}	Enable Setup Time for the Core Register	0.73	ns
t _{HE}	Enable Hold Time for the Core Register	0.00	ns
t _{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.60	ns
t _{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.62	ns
t _{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t _{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t _{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t _{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.23	ns
t _{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.30	ns
t _{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.30	ns
t _{CKMPWH}	Clock Minimum Pulse Width High for the Core Register	0.56	ns
t _{CKMPWL}	Clock Minimum Pulse Width Low for the Core Register	0.56	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-179 • AGL600 Global Resource

Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

		S	td.	
Parameter	Description	Min. ¹	Max. ²	Units
t _{RCKL}	Input Low Delay for Global Clock	1.48	1.82	ns
t _{RCKH}	Input High Delay for Global Clock	1.52	1.94	ns
t _{RCKMPWH}	Minimum Pulse Width High for Global Clock	1.18		ns
t _{RCKMPWL}	Minimum Pulse Width Low for Global Clock	1.15		ns
t _{RCKSW}	Maximum Skew for Global Clock		0.42	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).

2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).

3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-180 • AGL1000 Global Resource

Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

		S	td.	
Parameter	Description	Min. ¹	Max. ²	Units
t _{RCKL}	Input Low Delay for Global Clock	1.55	1.89	ns
t _{RCKH}	Input High Delay for Global Clock	1.60	2.02	ns
t _{RCKMPWH}	Minimum Pulse Width High for Global Clock	1.18		ns
t _{RCKMPWL}	Minimum Pulse Width Low for Global Clock	1.15		ns
t _{RCKSW}	Maximum Skew for Global Clock		0.42	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).

2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).

3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V DC Core Voltage

Table 2-181 • AGL015 Global ResourceCommercial-Case Conditions: TJ = 70°C, VCC = 1.14 V

		Std.		
Parameter	Description	Min. ¹	Max. ²	Units
t _{RCKL}	Input Low Delay for Global Clock	1.79	2.09	ns
t _{RCKH}	Input High Delay for Global Clock	1.87	2.26	ns
t _{RCKMPWH}	Minimum Pulse Width High for Global Clock	1.40		ns
t _{RCKMPWL}	Minimum Pulse Width Low for Global Clock	1.65		ns
t _{RCKSW}	Maximum Skew for Global Clock		0.39	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).

2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).

3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-182 • AGL030 Global Resource

Commercial-Case Conditions: $T_J = 70^{\circ}C$, VCC = 1.14 V

			Std.		
Parameter	Description	Ν	Min. ¹	Max. ²	Units
t _{RCKL}	Input Low Delay for Global Clock		1.80	2.09	ns
t _{RCKH}	Input High Delay for Global Clock		1.88	2.27	ns
t _{RCKMPWH}	Minimum Pulse Width High for Global Clock		1.40		ns
t _{RCKMPWL}	Minimum Pulse Width Low for Global Clock		1.65		ns
t _{RCKSW}	Maximum Skew for Global Clock			0.39	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).

2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).

3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Timing Waveforms



Figure 2-38 • FIFO Read







4 – Package Pin Assignments

UC81

Note: This is the bottom view of the package.

Note

For more information on package drawings, see PD3068: Package Mechanical Drawings.

Microsemi

Package Pin Assignments

CS81		CS81			
Pin Number	AGL030 Function	Pin Number	AGL030 Function		
A1	IO00RSB0	E1	GEB0/IO71RSB1		
A2	IO02RSB0	E2	GEA0/IO72RSB1		
A3	IO06RSB0	E3	GEC0/IO73RSB1		
A4	IO11RSB0	E4	VCCIB1		
A5	IO16RSB0	E5	VCC		
A6	IO19RSB0	E6	VCCIB0		
A7	IO22RSB0	E7	GDC0/IO32RSB0		
A8	IO24RSB0	E8	GDA0/IO33RSB0		
A9	IO26RSB0	E9	GDB0/IO34RSB0		
B1	IO81RSB1	F1	IO68RSB1		
B2	IO04RSB0	F2	IO67RSB1		
B3	IO10RSB0	F3	IO64RSB1		
B4	IO13RSB0	F4	GND		
B5	IO15RSB0	F5	VCCIB1		
B6	IO20RSB0	F6	IO47RSB1		
B7	IO21RSB0	F7	IO36RSB0		
B8	IO28RSB0	F8	IO38RSB0		
B9	IO25RSB0	F9	IO40RSB0		
C1	IO79RSB1	G1	IO65RSB1		
C2	IO80RSB1	G2	IO66RSB1		
C3	IO08RSB0	G3	IO57RSB1		
C4	IO12RSB0	G4	IO53RSB1		
C5	IO17RSB0	G5	IO49RSB1		
C6	IO14RSB0	G6	IO44RSB1		
C7	IO18RSB0	G7	IO46RSB1		
C8	IO29RSB0	G8	VJTAG		
C9	IO27RSB0	G9	TRST		
D1	IO74RSB1	H1	IO62RSB1		
D2	IO76RSB1	H2	FF/IO60RSB1		
D3	IO77RSB1	H3	IO58RSB1		
D4	VCC	H4	IO54RSB1		
D5	VCCIB0	H5	IO48RSB1		
D6	GND	H6	IO43RSB1		
D7	IO23RSB0	H7	IO42RSB1		
D8	IO31RSB0	H8	TDI		
D9	IO30RSB0	H9	TDO		

CS81			
Pin Number	AGL030 Function		
J1	IO63RSB1		
J2 IO61RSB1			
J3 IO59RSB1			
J4	IO56RSB1		
J5	IO52RSB1		
J6	IO45RSB1		
J7	ТСК		
J8 TMS			
J9 VPUMP			

Notes:

- 1. This is the bottom view of the package.
- 2. The die attach paddle center of the package is tied to ground (GND).

Note

For more information on package drawings, see PD3068: Package Mechanical Drawings.

Microsemi

Package Pin Assignments

QN48			
Pin Number AGL030 Func			
1	IO82RSB1		
2	GEC0/IO73RSB1		
3	GEA0/IO72RSB1		
4	GEB0/IO71RSB1		
5	GND		
6	VCCIB1		
7	IO68RSB1		
8	IO67RSB1		
9	IO66RSB1		
10	IO65RSB1		
11	IO64RSB1		
12	IO62RSB1		
13	IO61RSB1		
14	FF/IO60RSB1		
15	IO57RSB1		
16	IO55RSB1		
17	IO53RSB1		
18	VCC		
19	VCCIB1		
20	IO46RSB1		
21	IO42RSB1		
22	ТСК		
23	TDI		
24	TMS		
25	VPUMP		
26	TDO		
27	TRST		
28	VJTAG		
29	IO38RSB0		
30	GDB0/IO34RSB0		
31	31 GDA0/IO33RSB0		
32	GDC0/IO32RSB0		
33	VCCIB0		
34	GND		
35	VCC		
36 IO25RSB0			

QN48			
Pin Number	AGL030 Function		
37	IO24RSB0		
38 IO22RSB0			
39 IO20RSB0			
40 IO18RSB0			
41 IO16RSB0			
42 IO14RSB0			
43	IO10RSB0		
44	IO08RSB0		
45	IO06RSB0		
46 IO04RSB0			
47 IO02RSB0			
48	IO00RSB0		

Microsemi

IGLOO Low Power Flash FPGAs

QN132		QN132 QN		QN132	
Pin Number	AGL250 Function	Pin Number	AGL250 Function	Pin Number	AGL250 Function
A1	GAB2/IO117UPB3	A37	GBB1/IO38RSB0	B25	GND
A2	IO117VPB3	A38	GBC0/IO35RSB0	B26	IO54PDB1
A3	VCCIB3	A39	VCCIB0	B27	GCB2/IO52PDB1
A4	GFC1/IO110PDB3	A40	IO28RSB0	B28	GND
A5	GFB0/IO109NPB3	A41	IO22RSB0	B29	GCB0/IO49NDB1
A6	VCCPLF	A42	IO18RSB0	B30	GCC1/IO48PDB1
A7	GFA1/IO108PPB3	A43	IO14RSB0	B31	GND
A8	GFC2/IO105PPB3	A44	IO11RSB0	B32	GBB2/IO42PDB1
A9	IO103NDB3	A45	IO07RSB0	B33	VMV1
A10	VCC	A46	VCC	B34	GBA0/IO39RSB0
A11	GEA1/IO98PPB3	A47	GAC1/IO05RSB0	B35	GBC1/IO36RSB0
A12	GEA0/IO98NPB3	A48	GAB0/IO02RSB0	B36	GND
A13	GEC2/IO95RSB2	B1	IO118VDB3	B37	IO26RSB0
A14	IO91RSB2	B2	GAC2/IO116UDB3	B38	IO21RSB0
A15	VCC	B3	GND	B39	GND
A16	IO90RSB2	B4	GFC0/IO110NDB3	B40	IO13RSB0
A17	IO87RSB2	B5	VCOMPLF	B41	IO08RSB0
A18	IO85RSB2	B6	GND	B42	GND
A19	IO82RSB2	B7	GFB2/IO106PSB3	B43	GAC0/IO04RSB0
A20	IO76RSB2	B8	IO103PDB3	B44	GNDQ
A21	IO70RSB2	B9	GND	C1	GAA2/IO118UDB3
A22	VCC	B10	GEB0/IO99NDB3	C2	IO116VDB3
A23	GDB2/IO62RSB2	B11	VMV3	C3	VCC
A24	TDI	B12	FF/GEB2/IO96RSB2	C4	GFB1/IO109PPB3
A25	TRST	B13	IO92RSB2	C5	GFA0/IO108NPB3
A26	GDC1/IO58UDB1	B14	GND	C6	GFA2/IO107PSB3
A27	VCC	B15	IO89RSB2	C7	IO105NPB3
A28	IO54NDB1	B16	IO86RSB2	C8	VCCIB3
A29	IO52NDB1	B17	GND	C9	GEB1/IO99PDB3
A30	GCA2/IO51PPB1	B18	IO78RSB2	C10	GNDQ
A31	GCA0/IO50NPB1	B19	IO72RSB2	C11	GEA2/IO97RSB2
A32	GCB1/IO49PDB1	B20	GND	C12	IO94RSB2
A33	IO47NSB1	B21	GNDQ	C13	VCCIB2
A34	VCC	B22	TMS	C14	IO88RSB2
A35	IO41NPB1	B23	TDO	C15	IO84RSB2
A36	GBA2/IO41PPB1	B24	GDC0/IO58VDB1	C16	IO80RSB2

Note: This is the bottom view of the package.

Note

For more information on package drawings, see PD3068: Package Mechanical Drawings.

Package Pin Assignments

FG484			
AGL400 Function			
NC			
VCCIB1			
GND			
VCCIB3			
NC			
NC			
NC			
GND			
NC			
NC			
VCC			
VCC			
NC			
VCC			
VCC			
NC			
NC			
GND			
NC			
NC			